EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S48	3	("4631220"|"6406363"|"6609961").PN.	US-PGPUB; USPAT	OR	ON	2006/10/24 15:59
S50	6619	S49 and ("204" "205" "451").clas.	US-PGPUB; USPAT	OR	ON	2006/10/24 16:01
S53	21	S52 and greater with (center edge)	US-PGPUB; USPAT	OR	ON	2006/10/24 16:04
S52	368	S51 and (opening hole channel passage slot) with (electrolyte solution)	US-PGPUB; USPAT	OR	ON	2006/10/24 16:17
S55	11081	(pad WSID article medium) with (polishing electropolishing)	EPO; JPO; DERWENT	OR	ON	2006/10/24 16:19
S51	2154	S50 and (pad WSID article medium) with (opening hole channel passage slot)	US-PGPUB; USPAT	OR	ON	2006/10/24 16:19
S49	16737	(pad WSID article medium) with (polishing electropolishing)	US-PGPUB; USPAT	OR	ON	2006/10/24 16:19
S56	875	S55 and (pad WSID article medium) with (opening hole channel passage slot)	EPO; JPO; DERWENT	OR	ON	2006/10/24 16:20
S54	120	S51 and (opening hole passage) with (channel passage slot) with (electrolyte solution)	US-PGPUB; USPAT	OR	ON	2006/10/24 16:20
S58	338	Bulent near2 Basol cyprian near2 uzoh jeff near2 bogart	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/24 16:25
S57	30	S56 and (opening hole passage) with (channel passage slot) with (electrolyte solution)	EPO; JPO; DERWENT	OR	ON	2006/10/24 16:25
S59	63	S58 and (opening hole passage) with (channel passage slot) with (electrolyte solution)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/24 16:26

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	uzoh$-and$.in. and (semiconductor wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/24 16:45
L2	0	uzoh$-an$.in. and (semiconductor wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/24 16:45
L3	280	uzoh$.in. and (semiconductor wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/24 16:57
L4	0	"451".clas. and mask adj "plate."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/24 16:57
L5	12	"451".clas. and mask adj plate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/24 16:58
L6	1673	"451".clas. and channel and hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/24 16:59
L7	661	"451".clas. and channel and hole and (semiconductor wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/24 16:59
L8	326	"451".clas. and channel and hole and (semiconductor wafer) and width	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/24 16:59
L9	284	"451".clas. and channel and hole and (semiconductor wafer) and width and pad	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/24 17:00